# 1-of-8 Decoder/ Demultiplexer with LSTTL Compatible Inputs

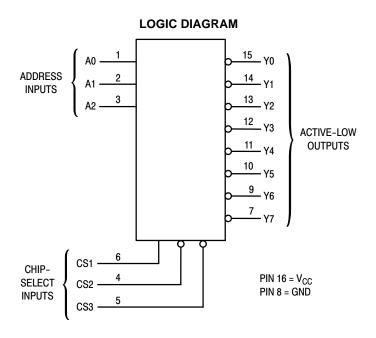
# **High-Performance Silicon-Gate CMOS**

The MC74HCT138A is identical in pinout to the LS138. The HCT138A may be used as a level converter for interfacing TTL or NMOS outputs to High Speed CMOS inputs.

The HCT138A decodes a three-bit Address to one-of-eight active-lot outputs. This device features three Chip Select inputs, two active-low and one active-high to facilitate the demultiplexing, cascading, and chip-selecting functions. The demultiplexing function is accomplished by using the Address inputs to select the desired device output; one of the Chip Selects is used as a data input while the other Chip Selects are held in their active states.

#### **Features**

- Output Drive Capability: 10 LSTTL Loads
- TTL/NMOS Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1.0 μA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 122 FETs or 30.5 Equivalent Gates
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant





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SOIC-16 D SUFFIX CASE 751B TSSOP-16 DT SUFFIX CASE 948F

#### **PIN ASSIGNMENT**

A0 [	1●	16	v <sub>cc</sub>
A1 [	2	15	70
A2 [	3	14	Y1
CS2 [	4	13	] Y2
CS3 [	5	12	1 Y3
CS1 [	6	11	] Y4
Y7 [	7	10	Y5
GND [	8	9	Y6
			₹,

# **MARKING DIAGRAMS**





TSSOP-16

A = Assembly Location

WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or = Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 5 of this data sheet.

Design Criteria	Value	Units
Internal Gate Count*	30.5	ea.
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	.0075	рJ

<sup>\*</sup>Equivalent to a two-input NAND gate.

#### **FUNCTION TABLE**

Inputs					Outputs								
CS1	CS2	CS3	<b>A2</b>	<b>A</b> 1	A0	Y0	Y1	Y2	<b>Y3</b>	Y4	Y5	Y6	Y7
Х	Χ	Н	Χ	Χ	Χ	Н	Н	Н	Н	Н	Н	Н	I
Х	Н	Χ	Χ	Χ	Χ	Н	Н	Н	Н	Н	Н	Н	Н
L	Χ	Χ	Χ	Χ	Χ	Н	Н	Н	Η	Н	Н	Н	Н
Н	L	L	L	L	L	L	Н	Н	Н	Н	Н	Н	Н
Н	L	L	L	L	Н	Н	L	Н	Н	Н	Н	Н	Н
Н	L	L	L	Η	L	Н	Н	L	Н	Н	Н	Н	Н
Н	L	L	L	Н	Н	Н	Н	Н	L	Н	Н	Н	Н
Н	L	L	Н	L	L	Н	Н	Н	Н	L	Н	Н	Н
Н	L	L	Н	L	Н	Н	Н	Н	Н	Н	L	Н	Н
Н	L	L	Н	Η	L	Н	Н	Н	Н	Н	Н	L	Н
Н	L	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L

H = high level (steady state)

L = low level (steady state)

X = don't care

# **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
I <sub>in</sub>	DC Input Current, per Pin	±20	mA
l <sub>out</sub>	DC Output Current, per Pin	±25	mA
Icc	DC Supply Current, V <sub>CC</sub> and GND Pins	±50	mA
P <sub>D</sub>	Power Dissipation in Still Air SOIC Package† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (TSSOP or SOIC Package)	260	°C

Unused outputs must be left open.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ).

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: –7 mW/°C from 65° to 125°C TSSOP Package: –6.1 mW/°C from 65° to 125°C

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types		+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)	0	500	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

# DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	Guaranteed Limit		
Symbol	Parameter	Test Conditions	v <sub>cc</sub>	–55 to 25°C	≤ <b>85</b> ° <b>C</b>	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out}$ = 0.1 V or $V_{CC}$ – 0.1 V $ I_{out}  \le 20 \mu A$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V <sub>IL</sub>	Maximum Low–Level Input Voltage	$V_{out}$ = 0.1 V or $V_{CC}$ – 0.1 V $ I_{out}  \le 20 \mu A$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$\begin{aligned} V_{in} &= V_{IH} \text{ or } V_{IL} \\  I_{out}  &\leq 20  \mu\text{A} \end{aligned}$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 4.0 \text{ mA}$	4.5	3.98	3.84	3.7	
V <sub>OL</sub>	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20 \mu A$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 4.0 \text{ mA}$	4.5	0.26	0.33	0.4	
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	±0.1	±1.0	±1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	5.5	4.0	40	160	μΑ
	Additional Ovices and Cumply	V <sub>in</sub> = 2.4 V, Any One Input		≥ <b>–</b> 55°C	25°C to	125°C	
$\Delta I_{CC}$	Additional Quiescent Supply Current	$V_{in} = V_{CC}$ or GND, Other Inputs $I_{out} = 0 \mu A$	5.5	2.9	2	.4	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

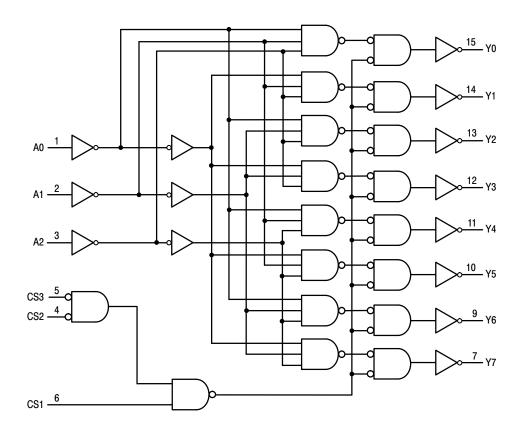
# AC ELECTRICAL CHARACTERISTICS (V<sub>CC</sub> = 5.0 V $\pm$ 10%, C<sub>L</sub> = 50 pF, Input $t_r$ = $t_f$ = 6.0 ns)

		Gu	Guaranteed Limit			
Symbol	Parameter	–55 to 25°C	≤ 85°C	≤ 125°C	Unit	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 4)	30	38	45	ns	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, CS1 to Output Y (Figures 2 and 4)	27	34	41	ns	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Output Transition Time, CS2 or CS3 to Output Y (Figures 3 and 4)	30	38	45	ns	
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 2 and 4)	15	19	22	ns	
t <sub>r</sub> , t <sub>f</sub>	Maximum Input Rise and Fall Time	500	500	500	ns	
C <sub>in</sub>	Maximum Input Capacitance	10	10	10	pF	

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Enabled Output)*	51	pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

# **EXPANDED LOGIC DIAGRAM**



# **SWITCHING WAVEFORMS**

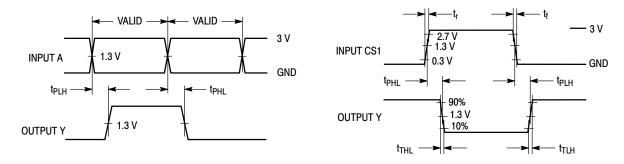


Figure 1. Figure 2.

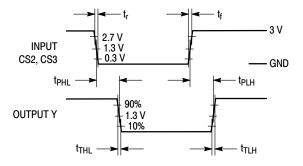
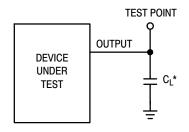


Figure 3.

# **TEST CIRCUIT**



\*Includes all probe and jig capacitance

Figure 4.

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HCT138ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HCT138ADR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
MC74HCT138ADTR2G	TSSOP-16 (Pb-Free)	2500 Units / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# **MECHANICAL CASE OUTLINE**



**DATE 29 DEC 2006** 

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

  MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

  SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

  DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
7	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

16. COLLECTOR 16. CATHODE 16. COLLECTOR, #4 16. EMITTER, #1  STYLE 5: STYLE 6: STYLE 7:  PIN 1. DRAIN, DYE #1 PIN 1. CATHODE 2. COMMON DRAIN (OUTPUT)  3. DRAIN, #1 2. CATHODE 2. COMMON DRAIN (OUTPUT)  4. DRAIN, #2 3. CATHODE 3. COMMON DRAIN (OUTPUT)  5. DRAIN, #3 5. CATHODE 4. GATE P-CH  7. DRAIN, #3 6. CATHODE 5. COMMON DRAIN (OUTPUT)  8. DRAIN, #4 7. CATHODE 7. COMMON DRAIN (OUTPUT)  8. DRAIN, #4 8. CATHODE 8. SOURCE P-CH  9. GATE, #4 9. ANODE 9. SOURCE P-CH  10. SOURCE, #4 10. ANODE 10. COMMON DRAIN (OUTPUT)  11. GATE, #3 11. ANODE 11. COMMON DRAIN (OUTPUT)  12. SOURCE, #3 12. ANODE 13. GATE N-CH  14. SOURCE, #2 14. ANODE 14. COMMON DRAIN (OUTPUT)  15. GATE, #1 15. ANODE 16. SOURCE N-CH  16. SOURCE, #1 16. ANODE 16. SOURCE N-CH	STYLE 1: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE	2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12.	CATHODE CATHODE ANODE NO CONNECTION CATHODE CATHODE NO CONNECTION	STYLE 3: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	COLLECTOR, DYE #1 BASE, #1 EMITTER, #1 COLLECTOR, #1 COLLECTOR, #2 BASE, #2 EMITTER, #2 COLLECTOR, #2 COLLECTOR, #3 BASE, #3 EMITTER, #3 COLLECTOR, #3 COLLECTOR, #4	STYLE 4: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	COLLECTOR, DYE #1 COLLECTOR, #1 COLLECTOR, #2 COLLECTOR, #3 COLLECTOR, #3 COLLECTOR, #4 COLLECTOR, #4 EMITTER, #4 BASE, #4 EMITTER, #4 BASE, #3 EMITTER, #3 BASE, #2 EMITTER, #2 BASE, #1		FOOTPRINT
STYLE 5:										
	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	DRAIN, #1 DRAIN, #2 DRAIN, #2 DRAIN, #3 DRAIN, #3 DRAIN, #3 DRAIN, #4 DRAIN, #4 GATE, #4 SOURCE, #4 GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2 GATE, #1	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE CATHODE ANODE	PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13. 14.	COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT GATE P-CH COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT SOURCE P-CH SOURCE P-CH COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT COMMON DRAIN (OUTPUT GATE N-CH COMMON DRAIN (OUTPUT GATE N-CH COMMON DRAIN (OUTPUT COMMON DRAIN COMMON DRAIN (OUTPUT COMMON DRAIN COMMON DRAIN COMMON DRAIN (OUTPUT COMMON DRAIN COMMON DRAIN COMMON DRAIN COMMON DRAIN COMMON DRAI	n n n n n n	16X 0.58	<u> </u>	16X 1.12

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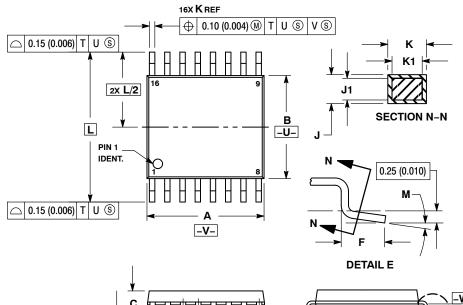
-T- SEATING PLANE





TSSOP-16 CASE 948F-01 ISSUE B

**DATE 19 OCT 2006** 



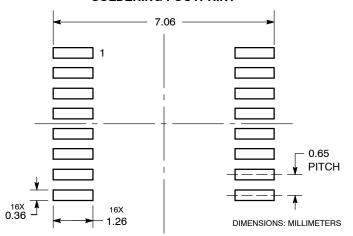
#### NOTES

- JIES:
  DIMENSIONING AND TOLERANCING PER
  ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSION A DOES NOT INCLUDE MOLD
  FLASH. PROTRUSIONS OR GATE BURRS.
  MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
C		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
7	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
Ы	6.40 BSC		0.252 BSC	
М	0 °	8 °	0 °	8 °

## **SOLDERING FOOTPRINT**

G



## **GENERIC MARKING DIAGRAM\***

168888888 XXXX XXXX **ALYW** 1<del>88888888</del>

XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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